

#### ABSTRACT OF THE DISCLOSURE

A silicon single crystal ingot is pulled at such a pull rate that the interior of the silicon single crystal ingot results in a perfect region in which agglomerates of interstitial silicon-type point defects and agglomerates of vacancy-type point defects are absent, while rotating a quartz crucible for storing a silicon melt at a predetermined rotation speed and rotating a silicon single crystal ingot pulled from the silicon melt in the opposite direction to the rotation of the quartz crucible at a predetermined rotation speed. An average rotation speed  $CR_{TAV}$  of the quartz crucible during the pulling of a top ingot portion of the silicon single crystal ingot is set to be faster than an average rotation speed  $CR_{BAV}$  of the quartz crucible during the pulling of a bottom ingot portion of the silicon single crystal ingot. This prevents generation of agglomerates of point defects in the pulling direction of the ingot and permits the pulled silicon single crystal ingot to have a perfect region substantially over the entire length and over the entire diameter.